

Product Overview

H11AG1M: 6-Pin DIP Phototransistor Output Optocoupler

For complete documentation, see the data sheet.

The H11AG1M series consists of a Gallium-Aluminum-Arsenide IRED emitting diode coupled with a silicon phototransistor in a dual in-line package. This device provides the unique feature of the high current transfer ratio at both low output voltage and low input current. This makes it ideal for use in low power logic circuits, telecommunications equipment and portable electronics isolation applications

Features

- High efficiency low degradation liquid epitaxial IRED
- Logic level compatible, input and output currents, with CMOS and LS/TTL
- High DC current transfer ratio at low input currents (as low as 200 μ A)
- Underwriters Laboratory (UL) recognized File#E90700, Volume 2
- VDE approval available as a test option
- – Add option V (e.g., H11AG1VM)

Applications

- Consumer Appliances
- Industrial Motor

Part Electrical Specifications

Product	Compliance	Status	Chan nels	CTR (Min) (%)	CTR (Max) (%)	CTR teste d @ IF (mA)	V _{CE(sat)} (Max) (V)	BV _{CE} (Min) (V)	BV _{CB} (Min) (V)	BV _{EC} (Min) (V)	t _{on} (Max) (μ s)	t _{off} (Max) (μ s)	V _{ISO} (Min) (V)	T _{OPR} (Min) (°C)	T _{OPR} (Max) (°C)	Pack age Type
H11AG1M	Pb-free	Active	1	300	-	1	0.4	30	70	7	5	5	4200	-40	100	PDIP -6
H11AG1SM	Pb-free	Active	1	300	-	1	0.4	30	70	7	5	5	4200	-40	100	PDIP -6
H11AG1SR2M	Pb-free	Active	1	300	-	1	0.4	30	70	7	5	5	4200	-40	100	PDIP -6
H11AG1TVM	Pb-free	Active	1	300	-	1	0.4	30	70	7	5	5	4200	-40	100	PDIP -6
H11AG1VM	Pb-free	Active	1	300	-	1	0.4	30	70	7	5	5	4200	-40	100	PDIP -6

For more information please contact your local sales support at www.onsemi.com.

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